

HEAT TREATMENT APPARATUS AND METHOD OF CALIBRATING THE APPARATUS

TECHNICAL FIELD

5 [0001]

This invention relates to a calibrating method for a heat treatment apparatus that performs a heat treatment to a process object, such as a semiconductor wafer. Particularly, the invention relates to a method of calibrating a thermal model of a heat treatment apparatus that estimates the temperature of a process object accommodated in the apparatus by using the thermal model and performs a control based on the estimation result.

15

BACKGROUND ART

[0002]

In a batch-type heat treating apparatus that performs a heat treatment, such as a film deposition process, an oxidation process or a diffusion process, to a number of semiconductor wafers collectively, process conditions, such as process temperature, process pressure and gas flow rate, are determined beforehand depending on the sort of a film to be formed and the film thickness, etc., and recipes describing the above process conditions are prepared. The operator selects a recipe corresponding to the sorts of a film and the film thickness, and the heat treatment apparatus operates under predetermined process conditions.

[0003]

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The heat treatment apparatus performs a treatment while controlling the process conditions, such as process temperature, process pressure, gas flow rate etc., so that they coincide with respective target values defined in the recipe. In order to perform the treatment, it is necessary to measure temperatures of the wafers, pressure in a heating furnace, gas flow rates and so on.

35

[0004]

The pressure in the heating furnace can be measured relatively precisely by a pressure gauge. Similarly, the gas flow rate can be measured relatively precisely by a mass-flow controller having a flowmeter or the like disposed in a supply pipe. However, it is difficult to measure wafer temperatures. For example, a technique of accommodating a wafer holding a temperature sensor in the heating furnace is conceivable. In this case, however, it becomes impossible to build a semiconductor element on a wafer's portion equipped with the temperature sensor. Moreover, there is a possibility that impurities originated from the temperature sensor contaminate the whole interior of the heating furnace, reducing a yield ratio of semiconductor devices.

[0005]

A technique for solving these problems is disclosed in Japanese Patent Publication JP2002-25997A and United States Patent No. 5, 517,594. With this technique, plural temperature sensors are arranged in a heating furnace. Based on the outputs of the temperature sensors and the electric power supplied to the heaters etc., temperatures of wafers are estimated momentarily by using a thermal model (mathematical model). The electric power supplied to the heaters is controlled by using the estimated values. According to this technique, it is possible to control a heat treatment apparatus while the temperatures of the wafers are estimated relatively precisely in non-contact manner.

[0006]

The thermal model for the above apparatus is established as follows. First, a thermal model (standard model) is made for a standard apparatus. Then, the standard model is applied to apparatuses having the same structure. Next, setup work is performed to compensate for a slight equipment-difference

(individual difference) between the standard apparatus and individual apparatuses. This work is carried out by performing a deposition process for setup by using each individual apparatuses, and by correcting the thermal model based on the
5 difference between the deposited film thickness and the target film thickness so that the individual apparatuses can form films of the same thickness irrespective of the equipment-difference among the individual apparatuses.

10 [0007]

The differences between the standard apparatus and the individual apparatuses include not only a difference relating to heat but also differences relating to gas flow rate and gas pressure. In other words, there are deviations in
15 measurements of the pressure gauge and the gas flowmeter among the individual apparatuses.

[0008]

Nevertheless, the conventional setup technique is
20 constructed so that the thermal-model correction also absorbs equipment-differences derived from all the factors except heat, and eliminates the individual difference among the apparatuses in appearance, in order to form the identical films in all the apparatuses. Such a setup technique is very effective, because
25 it is not necessary to perform in-depth analysis of the differences among the apparatuses in order to obtain apparatuses of substantially the same specification.

[0009]

30 In the above conventional setup technique, however, the thermal situation of the apparatus is not clear in some cases. For instance, if the thermal model cannot absorb the equipment-differences, it is not clear which part of the apparatus causes a deviation in the processing result (e.g.,
35 deviation in film thickness in the deposition process). In other words, it is impossible to grasp the thermal characteristics of

the individual apparatuses precisely.

DISCLOSURE OF THE INVENTION

[0010]

5 The present invention has been made under the
aforementioned circumstances, and an object of the present
invention is to enable more precise temperature estimation in a
heat treatment apparatus that estimates temperature of a
process object and performs a heat treatment based on the
10 estimated temperature.

 Another object of the present invention is to enable more
precise grasp of a thermal characteristics of a heat treatment
apparatus that estimates temperature of a process object and
performs a heat treatment based on the estimated temperature.

15

[0011]

 In order to attain the above objects, according to a first
aspect of the present invention, there is provided a calibrating
method for a heat treatment apparatus that includes a
20 processing vessel for accommodating a process object therein, a
plurality of heaters and a plurality of temperature sensors; that
stores a thermal model for estimating temperature of the
process object in the processing vessel based on outputs of the
temperature sensors; that estimates the temperature of the
25 process object in the processing vessel based on the outputs of
the temperature sensors by using the thermal model; and that
controls the heaters based on the estimated temperature, to
perform a heat treatment to the process object, said method
including the steps of: driving the heaters to heat an interior of
30 the processing vessel; measuring temperature in the processing
vessel; and calibrating the thermal model so that estimated
value of the temperature substantially coincide with the actual
measurement value of the temperature, upon comparison of the
measured temperature in the processing vessel with
35 temperature of the process object estimated by using the
thermal model.

[0012]

According to the above method, it is possible to calibrate the thermal model to be in conditions suitable for the heat treatment apparatus, allowing proper temperature estimation. Thus, a heat treatment process can be performed appropriately. In particular, it is possible to eliminate a deviation between the estimated temperature and the actual temperature which is caused by specific thermal characteristics of the heat treatment apparatus. Consequently, for example, if the change in temperature during a heat treatment process coincides with the change in estimated temperature while the processing result is disappointing one, it can be readily determined that the disappointing processing result is attributable to any factor except heat.

[0013]

In one embodiment, the processing vessel is capable of accommodating a plurality of process object; and the temperature measuring step includes a step of arranging the temperature sensors adjacent to the process objects and a step of measuring the temperatures of the process objects by means of the temperature sensors thus arranged.

[0014]

In one embodiment, the calibrating step calculate a correction value for the estimated value based on the measured temperature and the estimated temperature, and calibrates the thermal model so that the estimated value is corrected by using the correction value.

[0015]

In one embodiment, the heating step drives the heaters to sequentially set the interior of the processing vessel to preset temperatures of a plurality of levels; the temperature measuring step measures temperatures in the processing vessel at the

preset temperatures, respectively; a step of estimating the temperature of the process object estimates temperature of the interior of the processing vessel under the preset temperature of each of the levels; and the calibrating step calibrating step
5 calculates correction values for the estimated values based on the measured temperatures and the estimated temperatures, and calibrates the thermal model so that the estimated values estimated by the thermal model are corrected by using the correction values.

10

[0016]

In one embodiment, the thermal model has a function of estimating temperature of the heater and temperatures of the temperature sensors; and the calibrating step calculates a
15 correction value based on a relationship between an amount of change in the temperature of the heater and an amount of change in the measured temperature of each of the temperature sensors, and also based on a difference between the temperature of one of the temperature sensors located closest
20 to the heater estimated by using the thermal model and that actually measured, and calibrates the thermal model so that a estimated value is corrected based on the correction value.

[0017]

25 In one embodiment, an inside heater is arranged in the processing vessel; the thermal model has a function of estimating temperature of the inside heater; and the calibrating step calculates a correction value based on a relationship between an amount of change in the temperature of
30 the inside heater and an amount of change in the measured temperature of each of the temperature sensors, and also based on a difference between the temperature of one of the temperature sensors located closest to the inside heater estimated by using the thermal model and that actually
35 measured, and calibrates the thermal model so that a estimated value is corrected based on the correction value.

[0018]

In one embodiment, first and second heaters are arranged above and below the process object in the processing vessel, respectively; the thermal model has a function of estimating temperatures of the first and second heaters; and the calibrating step calculates a first correction value based on a relationship between an amount of change in the temperature of the first heater and an amount of change in the measured temperature of each of the temperature sensors, and also based on a difference between the temperature of one of the temperature sensors located closest to the first heater estimated by using the thermal model and that actually measured; and calculates a second correction value based on a relationship between an amount of change in the temperature of the second heater and an amount of change in the measured temperature of each of the temperature sensors, and also based on a difference between the temperature of one of the temperature sensors located closest to the second heater estimated by using the thermal model and that actually measured; and calibrates the thermal model so that a estimated value is corrected based on the first and second correction values.

The process object may be heat treated by estimating temperature in the processing vessel by using the thermal model calibrated by the above calibrating method, and by applying a heat treatment on a process object based on the estimated temperature.

30 [0019]

In order to attain the aforesaid object, according to the second aspect of the present invention, there is provided a heat treatment apparatus that includes a processing vessel for accommodating a process object therein, a plurality of heaters and a plurality of temperature sensors; that stores a thermal model for estimating temperature of the process object in the

processing vessel based on outputs of the temperature sensors; that estimates the temperature of the process object in the processing vessel based on the outputs of the temperature sensors by using the thermal model; and that controls the heaters based on the estimated temperature, to perform a heat treatment to the process object, said apparatus comprising: means for driving the heaters to heat an interior of the processing vessel; means for measuring temperatures of the process object in the processing vessel; and means for calibrating the thermal model so that estimated value of the temperature substantially coincide with the actual measurement value of the temperature, upon comparison of the measured temperature in the processing vessel with temperature of the process object estimated by using the thermal model.

According to the present invention, the thermal model is well-adapted to an individual treatment apparatus by customizing the thermal model according to the thermal characteristics of the individual heat treatment apparatus.

BRIEF DESCRIPTION OF THE DRAWINGS

[0020]

Fig. 1 is a view showing a constitution of a heat treatment apparatus in one embodiment of the present invention;

Fig. 2 is a diagram showing a constitution of a controller shown in Fig. 1;

Fig. 3 is a chart showing an example of data stored in a thermal model storage part and a recipe storage part shown in Fig. 2;

Fig. 4 is a graph showing an example of a setup recipe;

Fig. 5 is a view showing a constitution of a temperature measurement device;

Fig. 6 is a view showing a state where arm parts of the temperature measurement device are inserted into a boat;

Fig. 7 is a flow chart for explanation of a procedure that a standard thermal model is calibrated to produce a calibrated

thermal model;

Fig. 8 is a flow chart for explanation of a procedure that a standard thermal model is calibrated to produce a calibrated thermal model;

5 Fig. 9 is a table in which estimated temperatures estimated by the standard thermal model and actual temperatures are stored in coordination with respect to each preset temperature defined by a setup recipe; and

10 Fig. 10 is a graph for explanation of a method of correcting the standard thermal model.

DESCRIPTION OF REFERENCE SIGNS

[0021]

- 1 heat treatment apparatus
- 15 11 processing vessel
- 15 15 lower end
- 21 lid body
- 24 rotary table
- 26 boat
- 20 31 circumference heater
- 31a main heater
- 31b upper sub-heater
- 31c lower sub-heater
- 32 top heater
- 25 33 bottom heater
- 100 controller
- S1~S5 temperature sensors
- TC1~TC5 thermocouples (temperature sensors)

30 BEST MODE FOR CARRYING OUT THE INVENTION

[0022]

An embodiment where a batch-type heat treatment apparatus of the present invention is applied to a vertical heat treatment apparatus will be described.

35 As shown in Fig. 1, a vertical type heat treatment apparatus 1 in this embodiment includes a processing vessel

(reaction tube) 11. The processing vessel 11 is accommodates wafers W, which are process objects, to perform a designated heat treatment, for example, a CVD treatment, to the wafers W. The processing vessel 11 is formed of a heat-resistant and corrosion-resistant material, such as silica glass. The processing vessel 11 has a single-tube structure with its upper and lower ends being opened. The upper end of the single tube is narrowed to have a narrower diameter, forming an exhausting part 12. The exhausting part 12 is connected to a vacuum pump etc. through a not-shown exhaust pipe.

[0023]

A gas introductory part (introduction port) 13 for introducing a processing gas and an inert gas into the processing vessel 11 is arranged in a lower part of the processing vessel 11. One or more gas supply pipes 14 in communication with a gas source are inserted into the gas introductory part 13. The processing gas introduced from the gas introductory part 13 rises in the processing vessel 11, is used for a designated heat treatment of the wafers W, and then is discharged from the exhausting part 12.

[0024]

The lower end of the processing vessel 11 in a form of a flange is opened and closed by a lid body 21 formed of a heat-resistant, corrosion-resistant material, such as a stainless steel. The lid body 21 moved up and down by a not-shown elevator. The lid body 21 seals up the lower end 15 of the processing vessel 11 in its elevated position, and opens the lower end 15 of the processing vessel 11 in its lowered position. An O-ring 22 is interposed between the lower end 15 of the processing vessel 11 and the lid body 21 to ensure the air-tightness.

[0025]

A rotating post 23 stands up rotatably at a central part of

the lid body 21. A rotary table 24 is fixed to the upper end of the rotating post 23. A lower part of the lid body 21 is provided with a driving unit 25 for rotating the rotating post 23.

5 [0026]

Mounted on the rotary table 24 is a silica glass boat (wafer boat) 26, which is capable of holding e.g. sixty semiconductor wafers W at regular intervals with respect to the height direction. The boat 26 is mounted on the rotary table
10 24 when the lid body 21 is lowered. When the lid body 21 is moved up to seal up the lower end 15 of the processing vessel 11, the loading of wafers into the processing vessel 11 is completed. After completing a treatment, lowering of the lid body 21 allows the wafers to be unloaded. During the
15 treatment, the driving unit 25 rotates the rotary table 24 to rotate the wafers W, so that the wafers W are subjected to a uniform heat treatment.

[0027]

20 The processing vessel 11 is surrounded by a circumference heater 31 for heating the wafers W accommodated in the processing vessel 11 through its circumference. The circumference heater 31 is formed by e.g. rod-shaped resistance heating elements, which are arrayed in a
25 cylindrical form and are arranged in vertical posture so as to encircle the circumference of the processing vessel 11. The circumference heater 11 comprises a main heater 31a for heating the whole circumference of the processing vessel 11, an upper sub-heater 31b for heating a circumference of an upper
30 end portion of the processing vessel 11 and a lower sub-heater 31c for heating a circumference of a lower end portion of the processing vessel 11. The main heater 31a and the sub-heaters 31b and 31c are arranged in a circumferential direction of the processing vessel 11, alternately.

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[0028]

A top heater 32 and a bottom heater 33 are arranged above and below the processing vessel 11, respectively.

[0029]

5 The top heater 32 is provided to prevent temperature of the wafers from falling due to heat radiation of the processing vessel 11 on its exhaust side. The top heater 32 has a ring shape extending around the exhausting part 12, and is fixed to a support body 35 through supporting members 34.

10

[0030]

15 The bottom heater 33 is provided to prevent temperature of the wafers from falling due to heat radiation through the lid body 21, and is fixed to the lid body 21 through supporting members 34 to locate under the rotary table 24 in the processing vessel 11. The bottom heater 33 has a ring shape to allow the rotating post 23 to penetrate the center part of the heater 33.

20 [0031]

25 Three temperature sensors S1 to S3 are arranged in a vertical row on the circumference of the processing vessel 11. The temperature sensor S1 is arranged in a position corresponding to an upper section of the boat 26; the temperature sensor S2 in a position corresponding to an intermediate section of the boat 26; and the temperature sensor S3 is arranged in a position corresponding to a lower section of the boat 26.

30 [0032]

35 A temperature sensor S4 is arranged in a position between the top heater 32 and a top face of the boat 26 in the processing vessel 11. A temperature sensor S5 is arranged in a position between the bottom heater 33 and the rotary table 24 in the processing vessel 11. The temperature sensors S4 and S5 are accommodated in, for example, a silica tube to prevent

metal contamination.

[0033]

5 As mentioned later, outputs (detected temperatures) of the temperature sensors S1 to S5 are used to estimate respective surface temperatures of the wafers W on the boat 26, the top heater 32 and the bottom heater 33.

[0034]

10 The heat treatment apparatus 1 includes a controller 100 for performing a control operation of the whole apparatus.

[0035]

15 As shown in Fig. 2, the temperature sensors S1 to S5, an operating panel 121, pressure gauges (a group of gauges) 122, a heater controller 123, a mass-flow controller 124, a valve controller 125, a vacuum pump 126, etc. are all connected to the controller 100.

20 [0036]

As mentioned before, the temperature sensors S1 to S5 detect the temperatures of the outer wall surface of the processing vessel 11 and the temperatures of vicinities of the top heater 32 and the bottom heater 33, and send them to the
25 controller 100.

The operating panel 121 includes a display screen and operating buttons, transmits the operator's instructions to the controller 100, and displays various information from the controller 100 on the display screen.

30 The pressure gauges (a group of gauges) 122 detect pressures of respective parts in both the processing vessel 11 and the exhausting part 12, and send the detected values to the controller 100.

35 [0037]

The heater controller 123 is provided to control the

heaters 31a, 31b, 31c, 32 and 33 individually. In response to commands from the controller 100, the heater controller 123 energizes the heaters 31a, 31b, 31c, 32 and 33 to heat them. The heater controller 123 detects respective power
5 consumptions of the heaters 31a, 31b, 31c, 32 and 33 individually, and sends them to the controller 100.

[0038]

10 A mass-flow controller 124 is arranged in each pipe to control the flow rate of a gas flowing through the pipe to an amount instructed by the controller 100, and detects an actual flow rate of gas and sends it to the controller 100.

15 [0039]

A valve controller 125 is arranged in each pipe to control the opening of a valve disposed in each pipe to a value instructed by the controller 100. A vacuum pump 126 is connected to the exhausting part 12 of the processing vessel 11
20 through an exhaust pipe, and evacuates the interior of the processing vessel 11.

[0040]

As shown in Fig. 2, the controller 100 comprises a
25 thermal model storage part 111, a recipe storage part 112, a ROM 113, a RAM 114, an I/O port 115, a CPU 116, and a bus 117 connecting them with each other.

[0041]

30 As shown in Fig. 3(a), stored in the thermal model storage part 111 are a standard thermal model M1 which is made by using a standard apparatus having the same specification as that of the heat treatment apparatus 1, and a calibrated thermal model M2 which is made by calibrating
35 (customizing) the standard thermal model M1 to be adapted to this heat treatment apparatus 1. At the manufacturing of this

heat treatment apparatus 1, only the standard thermal model M1 is stored in the thermal model storage part 111 and subsequently, the calibrated thermal model M2 is stored with a setup procedure of the heat treatment apparatus 1.

5

[0042]

Each of the standard thermal model M1 and the calibrated thermal model M2 is a model (mathematical model; high-order multidimensional matrix) for estimating
10 temperatures in the processing vessel 11 based on the output signals (measured temperatures) of the temperature sensors S1 to S5, electric power supplied to the heaters 31a to 33 (i.e., instruction values representing electric power supplied from the heater controller 123 connected to the heaters 31a to 33) and
15 so on.

The standard thermal model M1 is one made by using the standard apparatus, which is commonly used by a plurality of heat treatment apparatuses 1 of the same specification. The calibrated thermal model M2 is one made by calibrating the
20 standard thermal model M1 to reflect the thermal characteristics of the individual apparatus, and is used for which is used for the actual operation (treatment).

[0043]

25 More in detail, based on the output signals (measured temperatures) of the sensors S1 to S5 and the electric power supplied to the heaters 31a to 33 etc., the standard thermal model M1 estimates: the temperatures of a center part P1 and a peripheral part P2 of a wafer W (boat top wafer) held on an
30 upper portion of the boat 26; the temperature of a center part P3 of a wafer W (boat center wafer) held on an intermediate portion of the boat 26; the temperatures of a center part P4 and a peripheral part P5 of a wafer W (boat bottom wafer) held on a lower portion of the boat 26 (i.e. temperatures in five positions
35 in total); the surface temperatures of the top heater 32 and the bottom heater 33; and the temperatures of the temperature

sensors S4 and S5. Note that the temperature of a peripheral part of the boat center wafer W is not measured, because the intermediate portion of the boat 26 is the most thermally-stable area where very little temperature difference exists between the center part P3 of the wafer W and its peripheral part and therefore, the temperature of the center part P3 of the boat center wafer can represent the temperatures of all the parts of the boat center wafer.

10 [0044]

The standard thermal model M1 calculates, by using respective estimated wafer temperatures, electric powers to be supplied to the heaters 31a to 33 in order to make the wafer temperatures equal to temperatures (target values) defined by a recipe. Note that, as to a technique of making the thermal model in itself, a technique disclosed in United State Patent 5,517,594 is available.

[0045]

20 The calibrated thermal model M2 has the same structure as the standard thermal model M1, except that the model M2 is customized in view of the thermal characteristics specific to this heat treatment apparatus 1 so that the model M2 can estimate the temperatures of respective parts precisely.

25

[0046]

As shown in Fig. 3(b), the recipe storage part 112 stores a setup recipe R1 and one or more process recipes R2.

30 [0047]

At the manufacturing of this heat treatment apparatus 1, only the setup recipe R1 is stored. The setup recipe R1 is executed when calibrating the standard thermal model M1 of the heat treatment apparatus 1. The setup recipe R1 defines the raise in temperature in the aforementioned positions P1 to P5 with respect to time in a step-like manner as shown in Fig. 4.

35

The process recipes R2 are prepared for respective heat treatments (processes) performed by a user.

[0048]

5 The ROM 113 shown in Fig. 2 is a storage medium such as an EEPROM, a flash memory and/or a hard disc drive, and stores an operation program etc. for the CPU 116. The RAM 114 functions as a working area etc. for the CPU 116.

10 [0049]

 The I/O port 115 is connected to the temperature sensors S1 to S5, the operating panel 121, the pressure gauges 122, the heater controller 123, the mass-flow controllers 124 and the valve controller 125 to control the inputting and outputting of
15 data, signals, etc.

[0050]

 The bass 117 transmits information among respective parts.

20

[0051]

 The CPU (Central Processing Unit) 116 is a center of the controller 100, executing control programs stored in the ROM 113 and controls the operation of the heat treatment apparatus
25 1 in accordance with a recipe stored in the recipe storage part 112, to follow the instructions from the operating panel 121.

[0052]

30 Next, a temperature measurement apparatus 51 used in the setup operation of the heat treatment apparatus 1 will be described.

 As shown in Fig. 5, the temperature measurement apparatus 51 includes a supporting column 52, and first, second and third arms 53, 54, 55 all extending from the supporting column 52 horizontally. As shown in Fig. 6, the first to third
35 arms 53, 54, 55 are arranged in positions to allow them to be

inserted sideways into an upper slot, a center slot and a lower slot of the boat 26, respectively. The first to third arms 53 to 55 are equipped with thermocouples (temperature sensors) TC1 to TC5.

5

[0053]

On the first arm 53, the thermocouples TC1 and TC2 are arranged in positions that respectively oppose the center part P1 and the peripheral part P2 of the wafer W in an upper slot of the boat 26 when the arm 53 is inserted into the boat 26.

10

[0054]

On the second arm 54, the thermocouple TC3 is arranged in a position that opposes the center part P3 of the wafer W in a center slot of the boat 26 when the arm 54 is inserted into the boat 26.

15

On the third arm 55, the thermocouples TC4 and TC5 are arranged in positions that respectively oppose the center part P4 and the peripheral part P5 of the wafer W in a lower slot of the boat 26 when the arm 55 is inserted into the boat 26.

20

[0055]

The thermocouples TC1 to TC5 are arranged in the vicinity of respective temperature-monitoring wafers (boat-upper-slot wafer, boat-center-slot wafer and boat-lower-slot wafer) W in non-contact manner, and are capable of measuring the surface temperatures of areas P1 to P5 of the wafers W to be subjected to temperature measurement. Output signal lines of these thermocouples TC are connected to the I/O port 115 of the controller 100, when the setup operation is performed.

30

[0056]

Next, the setup operation of the heat treatment apparatus 1 will be described with reference to flow charts of Fig. 7 and Fig. 8. This setup operation is an operation to detect differences in thermal characteristics between the individual

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heat treatment apparatus 1 and the standard apparatus due to delicate differences therebetween, and calibrates the standard thermal model M1 stored in the thermal model storage part 111 to make a calibrated thermal model M2 specific to the heat
5 treatment apparatus 1.

[0057]

First, by an operator, the lid body 21 is lowered to mount the boat 26 holding dummy wafers W on the rotary table 24.
10 The temperature measurement apparatus 51 is inserted into the boat 26 sideways. Next, the lid body 21 is moved up to load the boat 26 into the processing vessel 11.

[0058]

15 Next, the operator instructs to start the calibration of the standard thermal model M1 by means of the operating panel 121.

In response to this instruction, the controller 100 (the CPU 116) starts the operation in accordance with a calibration
20 program stored in the ROM 113.

[0059]

First, the controller 100 controls the valve controller 125, the vacuum pump 126, etc. while monitoring the output of the
25 pressure gauge 122 to evacuate the interior of the processing vessel 11 to a designated pressure (step S11).

[0060]

Next, according to the setup recipe R1, temperatures in
30 the areas P1 to P5 of the wafers W in the processing vessel 11 are set to a first temperature (e.g., 400 °C) (step S12).

[0061]

At that time when temperatures of the wafers W are stabilized, the actual temperatures in the positions P1 to P5 of
35 the center parts and the peripheral parts of respective the temperature-monitoring wafers W are measured by using the

thermocouples TC1 to TC5 (step S13). While, temperatures in the positions P1 to P5 of the center parts and the peripheral parts of respective temperature-monitoring wafers W are estimated by using the standard thermal model M1 (step S14).

5 Next, the measured values (actual measurement values), the estimated values and the correspondence therebetween are stored in the RAM 114 (step S15).

[0062]

10 Next, it is judged whether or not treatments for all temperatures defined by the setup recipe R1 have been completed (step S16). If not completed, in other words, a treatment(s) for a certain set temperature is left undone (in step S16, "No"), the routine returns to step S12 where the
15 similar treatment for the set temperature is repeated.

[0063]

On the other hand, when the treatments for all temperatures defined in the setup recipe R1 (step S16; Yes),
20 the routine goes to step S18. At this time, a correspondence table showing the correspondence between the measured values and the estimated values shown in Fig. 9 has been made in the RAM 114.

25 [0064]

At step 18, based on the correspondence table made in the RAM 114, the temperatures TR1 to TR5 measured by the thermocouples TC1 to TC5 are compared with the temperatures TP1 to TP5 estimated by using the standard thermal model M1,
30 respectively, and correction values for the temperatures of the wafers W are calculated.

[0065]

Although any technique may be used for calculating the
35 correction values, they may be calculated, for example, in accordance with the following mathematical expression 1.

[Expression 1]

Correction value $i = T_{Pi}$ (estimated value by the standard thermal model M1) $- T_{ri}$ (measured value)

5 where i : the number (1-5) indicating temperature-estimation areas (P1 to P5)

[0066]

10 Note that the correction value may be a fixed value or may be in a form of a function. For instance, if "estimated value T_{Pi} minus measured value T_{ri} " varies widely as shown in Fig. 9, a linear function $f(T)$ (T : estimated temperature by the standard thermal model M1) that represents the correction values may be derived by using least squares method, for
15 example.

[0067]

20 Next, the standard thermal model M1 is calibrated (step S19). That is, the standard thermal model M1 is corrected so that values represented by the following expression 2 coincide with the estimated values respectively.

[Expression 2]

25 Estimated temperature $i = \text{Temperature } i \text{ estimated by the standard thermal model M1} - \text{Correction value } i$

[0068]

30 For instance, if the correction values are represented by a function $f(T)$ as shown in Fig. 10 and a temperature estimated by the standard thermal model M1 is T_0 , the standard thermal model M1 is corrected so that a estimated temperature becomes " $T_0 - f(T_0)$ ".

[0069]

35 Next, the standard thermal model M1 is corrected so that it is capable of precise estimation of the surface temperatures of the top heater 32 and the bottom heater 33 in the processing

vessel 11 (step S20). This correcting operation will be described with reference to Fig. 8.

First, the temperature in the processing vessel 11 is controlled to be maintained at a predetermined constant value
 5 Tcons, waiting for the system being stabilized. Next, with the use of the standard thermal model M1 before renewal, temperatures of the temperature sensors S4 and S5 are estimated. In addition, the temperature of the temperature sensors S4 and S5 are measured (step S21).

10

[0070]

Next, the estimated values and the measured values of the temperatures of the temperature sensors S4 and S5 are compared, and correction values are calculated in a manner
 15 similar to that shown by expression 1 (step S22).

[0071]

Then, as for the top heater 32, a correlation between a variation ΔT_t of the surface temperature of the top heater 32
 20 and variations ΔT_{s1} to ΔT_{s5} of the temperatures of the sensors S1 to S5 is obtained by using a system model including the heater controller 123 (step S23).

That is, a matrix K_t (expression 3) satisfying the following expression 4 is derived.

25

[Expression 3]

$$K_t = [K_{t1}, K_{t2}, K_{t3}, K_{t4}, K_{t5}]$$

[Expression 4]

$$30 \quad \Delta T_t = [K_{t1}, K_{t2}, K_{t3}, K_{t4}, K_{t5}] \cdot \begin{bmatrix} \Delta T_{s1} \\ \Delta T_{s2} \\ \Delta T_{s3} \\ \Delta T_{s4} \\ \Delta T_{s5} \end{bmatrix}$$

[0072]

Then, as for the bottom heater 33, a correlation between a variation ΔT_b of the surface temperature of the bottom heater 33 and variations ΔT_{s1} to ΔT_{s5} of the temperatures of the sensors S1 to S5 is obtained by using a system model including the heater controller 123 (step S23).

That is, a matrix K_b (Expression 5) satisfying the following expression 6 is derived.

[Expression 5]

$$K_b = [K_{b1}, K_{b2}, K_{b3}, K_{b4}, K_{b5}]$$

[Expression 6]

$$\Delta T_b = [K_{b1}, K_{b2}, K_{b3}, K_{b4}, K_{b5}] \cdot \begin{bmatrix} \Delta T_{s1} \\ \Delta T_{s2} \\ \Delta T_{s3} \\ \Delta T_{s4} \\ \Delta T_{s5} \end{bmatrix}$$

15 [0073]

Next, the standard thermal model M1 is calibrated by applying the above correlations to portions, which relate to the estimation of the temperature of the top heater 32 and the same of the bottom heater 33, of the standard thermal model

20 M1, as shown by the following expressions 7 and 8 (step S24).

[Expression 7]

Temperature of the top heater 32 =

Temperature estimated by standard thermal model M1 +

$$25 \quad [K_{t1}, K_{t2}, K_{t3}, K_{t4}, K_{t5}] \cdot \begin{bmatrix} 0 \\ 0 \\ 0 \\ \text{Estimated Temperature of Temperature Sensor S4} \\ - \\ \text{Measured Temperature of Temperature Sensor S4} \\ 0 \end{bmatrix}$$

[Expression 8]

Temperature of the bottom heater 33 =

Temperature estimated by standard thermal model M1 +

5

$$[Kb1, Kb2, Kb3, Kb4, Kb5] \cdot \begin{bmatrix} 0 \\ 0 \\ 0 \\ \text{Estimated Temperature of Temperature Sensor S5} \\ - \\ \text{Measured Temperature of Temperature Sensor S5} \\ 0 \end{bmatrix}$$

[0074]

10 In the above way, the process of calibrating (customizing) the standard thermal model M1 for this apparatus is completed. Then, the loaded boat 26 is unloaded.

[0075]

15 The so-customized standard thermal model M1, namely, a calibrated thermal model M2 is stored in the thermal model storage part 111 (step S25), and is subsequently used for estimating the temperatures in the positions P1 to P5 of the wafers W and the surface temperatures of the top heater 32 and the bottom heater 33.

20

[0076]

25 When performing a process by the heat treatment apparatus 1 thus set up, a process recipe R2 corresponding to the process to be performed is stored in the recipe storage part 112. Then, the process is carried out while estimating the temperatures of the wafers W, the top heater 32 and the bottom heater 33 by using the calibrated thermal model M2. As the calibrated thermal model M2 has been calibrated for this heat treatment apparatus 1, it is possible to estimate the

temperatures of the wafers W and the heaters 32 and 33 precisely. Further, if the process result should be out of the allowable range, it is possible to readily discriminate whether the result is caused by a thermal factor or the other factor.

5

[0077]

Note that this invention is not limited to the above-mentioned embodiment, and various modifications and applications are possible. For instance, the invention may be modified as follows: measuring the temperatures of the top heater 32 and the bottom heater 33 by means of e.g., radiation thermometers or the like; calculating correction values based on estimated values by using the standard thermal model M1 and actually-measured values by using the radiation thermometers; and correcting the estimated temperatures by using the correction values.

[0078]

The number of temperature sensors for the estimation and the arrangement of the sensors may be modified. The number of the temperature sensors is not limited to five. The temperature sensors may be arranged on an inner surface of the wall of the processing vessel 11.

25 [0079]

The heat treatment apparatus 1 on application of the present invention may be optionally modified, without being limited to the above-mentioned embodiment. For instance, the processing vessel 1 may be of a double-tube structure. The boat 26 may be modified so that the number of semiconductor wafers W accommodated therein is more than (e.g., about 100 to 150 pcs.) or less than (e.g., 15 to 30 pcs.) that shown in the embodiment.

35 [0080]

Although the present invention has been described with

the above-mentioned embodiment taking a CVD apparatus as an example, any sort of treatment is possible. The present invention is applicable not only to a CVD apparatus but also to various sorts of batch-type heat treatment apparatuses, such as
5 an oxidation apparatus and an etching apparatus.

[0081]

The constitution and operations of instruments are not limited to those in the above-mentioned embodiment. For
10 instance, although the above-mentioned embodiment is provided with three sidewall heaters and two inner heaters, the number and arrangement of the heaters are optional. The heater is not limited to a resistant heater, and may be a lamp. The arrangement for measuring the temperature of the wafers
15 and the like is not limited to a thermocouple, and any sort of temperature sensor is applicable.

[0082]

The thermal model and its design technique is not limited
20 to those disclosed in United Stated Patent No.5,517,594, and any model and any design technique are applicable.

[0083]

At least a part of the computer program for performing
25 the above-mentioned calibration process may be stored in a computer-readable recording medium for distribution, such as CD-ROM and DVD-ROM, may be transferred to the RAM 114 through the I/O port 115, and may be executed by the CPU 116, to carry out the above calibration process. Alternatively, the
30 program may be transferred to the I/O port 115 through a network.